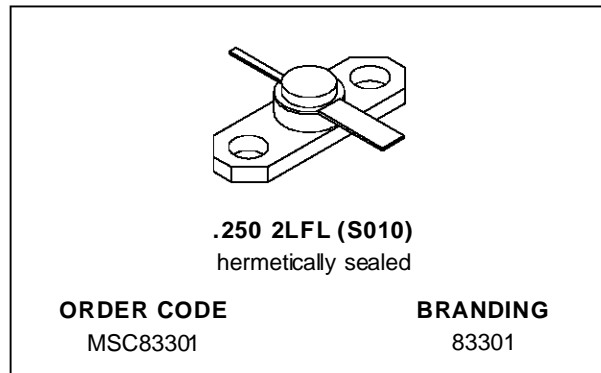


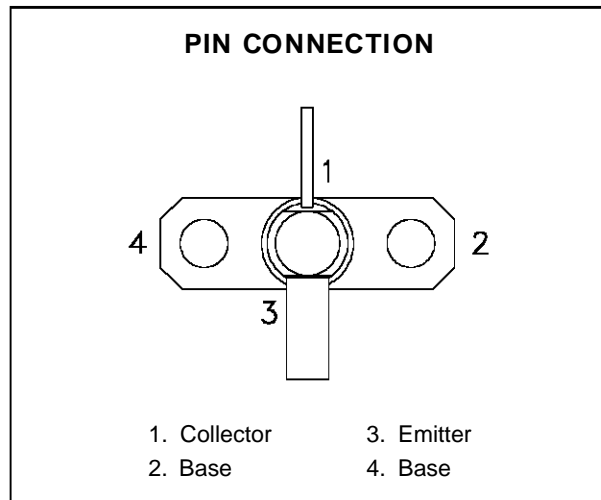
RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- VSWR CAPABILITY $\infty:1$ @ RATED CONDITIONS
- HERMETIC STRIPAC[®] PACKAGE
- $P_{OUT} = 1.0$ W MIN. WITH 7.0 dB GAIN @ 3.0 GHz



DESCRIPTION

The MSC83301 is a common base hermetically sealed silicon NPN microwave power transistor utilizing an overlay, emitter site ballasted geometry with a refractory gold metallization system. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions. The MSC83301 is designed for Class C amplifier/oscillator applications in the 1.0 - 3.0 GHz frequency range.



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_c \leq 50^{\circ}C$)	6.0	W
I_c	Device Current*	200	mA
V_{CC}	Collector-Supply Voltage*	30	V
T_J	Junction Temperature	200	$^{\circ}C$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}C$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	25	$^{\circ}C/W$
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*Applies only to rated RF amplifier operation

MSC83301

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

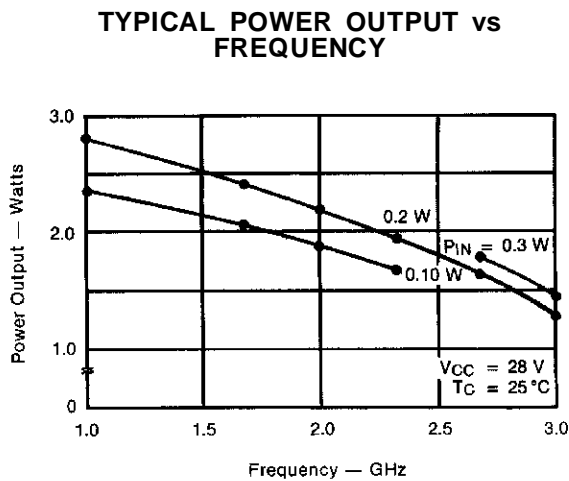
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 1 mA	I _E = 0 mA	45	—	—	V
BV _{EBO}	I _E = 1 mA	I _C = 0 mA	3.5	—	—	V
BV _{CER}	I _C = 5 mA	R _{BE} = 10 Ω	45	—	—	V
I _{CBO}	V _{CB} = 28V		—	—	0.5	mA
h _{FE}	V _{CE} = 5 V	I _C = 100 mA	30	—	300	—

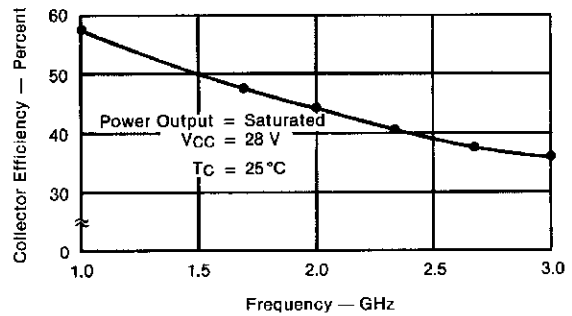
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 3.0 GHz	P _{IN} = 0.20 W	V _{CC} = 28 V	1.0	1.3	—	W
η _C	f = 3.0 GHz	P _{IN} = 0.20 W	V _{CC} = 28 V	33	36	—	%
P _G	f = 3.0 GHz	P _{IN} = 0.20 W	V _{CC} = 28 V	7.0	8.1	—	dB
C _{OB}	f = 1 MHz	V _{CB} = 28 V		—	—	3.5	pF

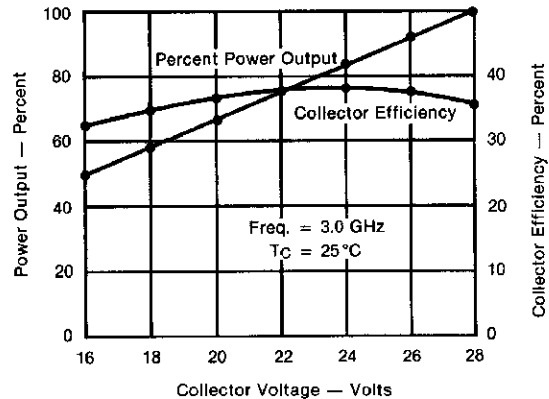
TYPICAL PERFORMANCE



TYPICAL COLLECTOR EFFICIENCY vs FREQUENCY

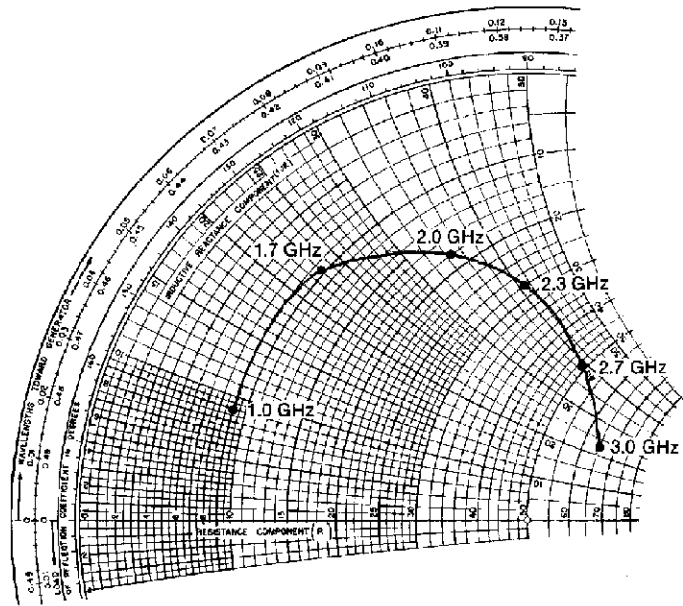
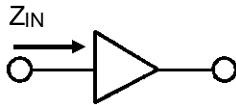


PERCENT POWER OUTPUT & COLLECTOR EFFICIENCY vs COLLECTOR VOLTAGE



IMPEDANCE DATA

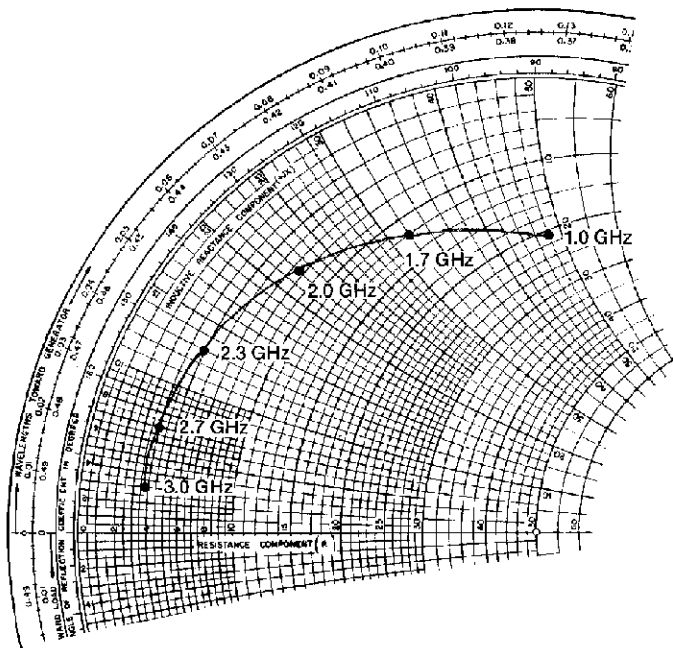
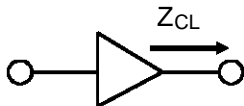
TYPICAL INPUT IMPEDANCE



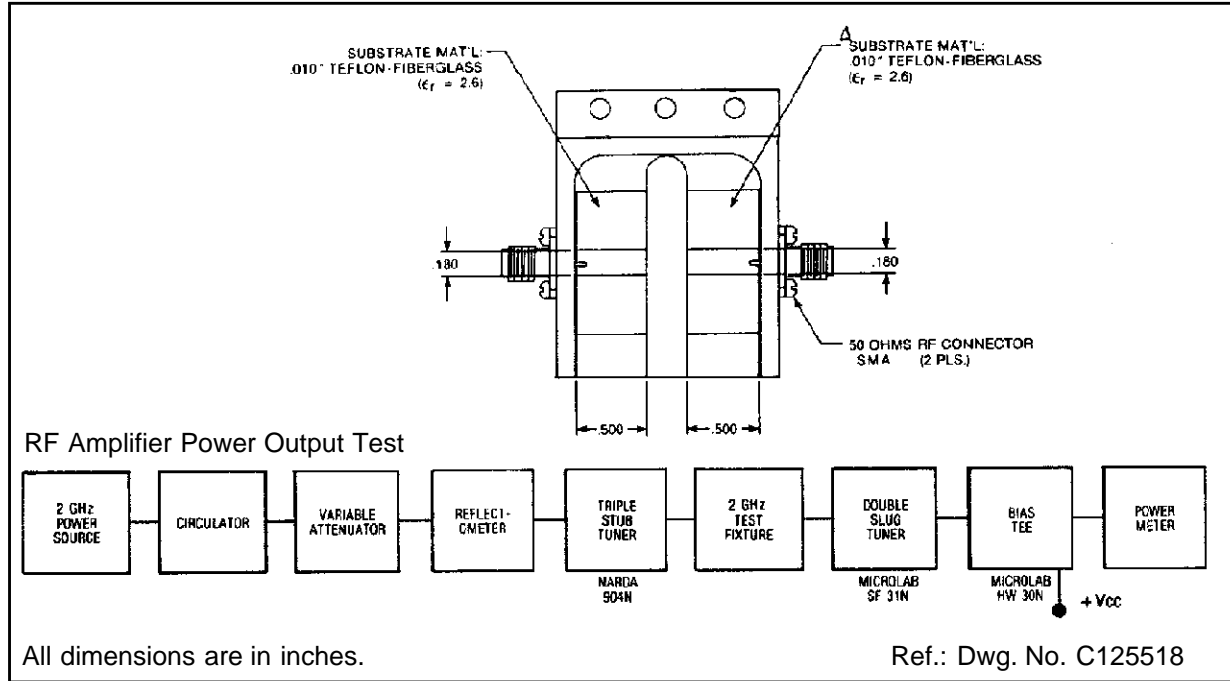
FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)
1.0 GHz	9.0 + j 9.0	21.0 + j 48.0
1.7 GHz	9.5 + j 23.0	12.0 + j 32.0
2.0 GHz	18.0 + j 34.5	7.5 + j 22.0
2.3 GHz	28.0 + j 41.0	5.0 + j 13.0
2.7 GHz	49.0 + j 39.0	4.0 + j 7.0
3.0 GHz	65.0 + j 22.0	3.8 + j 3.0

P_{OUT} = Saturated
 V_{CC} = 28 V
 Normalized to 50 ohms

TYPICAL COLLECTOR LOAD IMPEDANCE

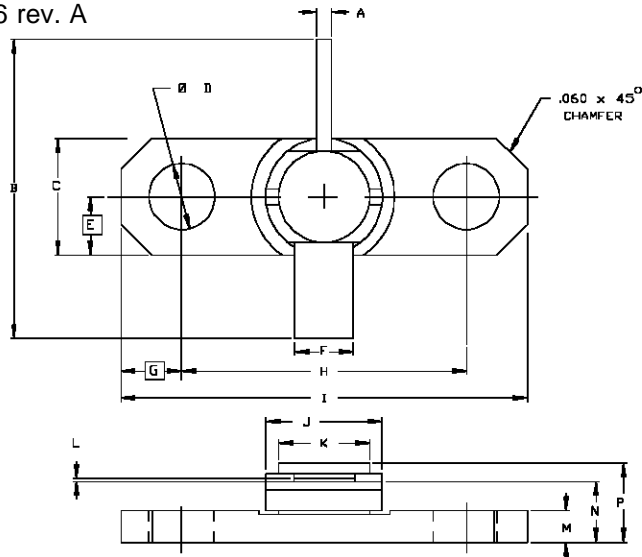


TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0216 rev. A



SGS-THOMSON MICROELECTRONICS		CONT'D			
	MINIMUM Inches/mm	MAXIMUM Inches/mm	MINIMUM Inches/mm	MAXIMUM Inches/mm	
A	.028/0,71	.032/0,81	K	165/4,19	185/4,70
B	.740/18,80		L	.003/0,08	.007/0,18
C	.245/6,22	.255/6,48	M	.058/1,47	.068/1,73
D	.128/3,25	.132/3,35	N	.119/3,02	.135/3,43
E	.125/3,18		P	.149/3,78	.187/4,75
F	.110/2,79	.117/2,97			
G	.117/2,97				
H	.560/14,22	.570/14,48			
I	.795/20,19	.805/20,45			
J	.225/5,72	.235/5,97			

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